

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1693	438/197.ccls. or 438/585.ccls. or 438/652.ccls.	USPAT	OR	ON	2005/07/06 17:00
L2	1822	438/655.ccls. or 438/660.ccls. or 438/664.ccls. or 438/682.ccls.	USPAT	OR	ON	2005/07/06 17:00
L3	1937	438/684.ccls. or 438/758.ccls. or 438/778.ccls. or 438/787.ccls.	USPAT	OR	ON	2005/07/06 17:01
L4	328	438/791.ccls.	USPAT	OR	ON	2005/07/06 17:01
L5	5415	1 or 2 or 3 or 4	USPAT	OR	ON	2005/07/06 17:01
L6	3810	5 and (nitrid\$3 or carbon\$5)	USPAT	OR	ON	2005/07/06 17:01
L7	135	6 and ((gate adj insulator) and (gate adj electrode))	USPAT	OR	ON	2005/07/06 17:02
S1	22581	substrate and gate and ((gate adj oxide) or (gate adj insulator) or (gate adj insulating)) and (gate adj electrode)	USPAT	OR	ON	2004/12/21 15:10
S2	29	S1 and ((nitriding or carbonizing) with (sidewall or (side adj wall)))	USPAT	OR	ON	2004/12/17 19:11
S3	2	(metal with (gate adj electrode)) and (itriding or carbonizing) and ((side adj wall) or sidewall)	USPAT	OR	ON	2004/12/16 13:11
S4	2	((("6489236") or ("5966606")).PN.	USPAT	OR	OFF	2004/12/16 13:35
S5	281	gate and nitride and (tantalum or titanium) and (gate with (sidewall or (side adj wall)) with nitrid\$8) and ammonia	USPAT	OR	ON	2004/12/16 13:40
S6	457	gate and nitride and (tantalum or titanium) and (gate with (sidewall or (side adj wall)) with nitrid\$8) and ammonia	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 13:37
S7	407	S6 and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 13:42
S8	141	S7 and (nitridiz\$5 or nitrided or nitriding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 13:42
S9	336	gate and nitride and (tungsten or tantalum or titanium) and (gate with (sidewall or (side adj wall)) with nitrid\$8) and ammonia	USPAT	OR	ON	2004/12/16 13:41

S10	561	gate and nitride and (tungsten or tantalum or titanium) and (gate with (sidewall or (side adj wall)) with nitrid\$8) and ammonia	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 13:41
S11	486	S10 and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 13:42
S12	150	S11 and (nitridiz\$5 or nitrided or nitriding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 15:52
S13	40	S12 and ((nitridiz\$5 or nitrided or nitriding) with temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/17 17:15
S14	2	((("6284634") or ("6197702")).PN.	USPAT	OR	OFF	2004/12/17 19:04
S15	22581	substrate and gate and ((gate adj oxide) or (gate adj insulator) or (gate adj insulating)) and (gate adj electrode)	USPAT	OR	ON	2004/12/17 19:11
S16	0	S15 and ((carbonizing) with (sidewall or (side adj wall)))	USPAT	OR	ON	2004/12/17 19:12
S17	7	(carbonizing with (sidewall or (side adj wall)))	USPAT	OR	ON	2004/12/17 19:12
S18	17	(sidewall or (side adj wall)) with (carbonized or carbonised or carbonizing or carbonising)	USPAT	OR	ON	2004/12/17 19:13
S19	2002	(sidewall or (side adj wall)) with (carbon\$5)	USPAT	OR	ON	2004/12/17 19:14
S20	133	S19 and (gate adj electrode)	USPAT	OR	ON	2004/12/17 19:17
S21	4	S20 and carbonized	USPAT	OR	ON	2004/12/17 19:17
S22	219	(carbonizing or carbonided or carbonized or carbonised) and (carbon with gas) and ((sidewall or (side adj wall)) or (gate adj electrode))	USPAT	OR	ON	2004/12/20 17:00
S23	0	methane with carbonize with sidewall	USPAT	OR	ON	2004/12/20 17:00
S24	20	methane and carbonize and sidewall	USPAT	OR	ON	2004/12/20 17:01

S25	244	(silicon adj carbide) with (sidewall or (side adj wall))	USPAT	OR	ON	2004/12/20 17:04
S26	18	S25 and methane	USPAT	OR	ON	2004/12/20 17:17
S27	1957	(gate adj electrode) and (polycrystalline adj silicon) and (metal adj silicide)	USPAT	OR	ON	2004/12/20 18:20
S28	540	S27 and (titanium adj silicide)	USPAT	OR	ON	2004/12/20 18:23
S29	263	(metal adj silicide).ti.	USPAT	OR	ON	2004/12/20 18:24
S30	84	S29 and (polycrystalline adj silicon)	USPAT	OR	ON	2004/12/20 18:41
S31	2	S30 and nitriding	USPAT	OR	ON	2004/12/20 18:24
S32	72	(gate adj electrode) with undercutting	USPAT	OR	ON	2004/12/20 18:41
S33	1542	438/197.ccls. or 438/585.ccls. or 438/652.ccls.	USPAT	OR	ON	2005/07/06 17:00
S34	1751	438/655.ccls. or 438/660.ccls. or 438/664.ccls. or 438/682.ccls.	USPAT	OR	ON	2005/07/06 17:00
S35	1806	438/684.ccls. or 438/758.ccls. or 438/778.ccls. or 438/787.ccls.	USPAT	OR	ON	2005/07/06 17:01
S36	309	438/791.ccls.	USPAT	OR	ON	2005/07/06 17:01
S37	134	(semiconductor adj substrate) and (gate adj electrode) and (oxidizing with plasma)	USPAT	OR	ON	2004/12/21 15:50
S38	63	(damage with restor\$5) and (gate adj electrode) and ((insulation or insulator or insulating) adj film)	USPAT	OR	ON	2004/12/21 16:51
S39	2	((damage with restor\$5) with oxidizing) and (gate adj electrode)	USPAT	OR	ON	2004/12/21 16:52
S40	3	((damage with restor\$5) with oxidizing)	USPAT	OR	ON	2004/12/21 16:52